

PZT222A

NPN Silicon Planar Epitaxial Transistor

This NPN Silicon Epitaxial transistor is designed for use in linear and switching applications. The device is housed in the SOT-223 package which is designed for medium power surface mount applications.

Features

- PNP Complement is PZT2907AT1
- The SOT-223 Package Can be Soldered Using Wave or Reflow
- SOT-223 Package Ensures Level Mounting, Resulting in Improved Thermal Conduction, and Allows Visual Inspection of Soldered Joints
- The Formed Leads Absorb Thermal Stress During Soldering, Eliminating the Possibility of Damage to the Die
- Available in 12 mm Tape and Reel
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Collector-Base Voltage	V_{CBO}	75	Vdc
Emitter-Base Voltage (Open Collector)	V_{EBO}	6.0	Vdc
Collector Current	I_C	600	mAdc
Total Power Dissipation up to $T_A = 25^\circ\text{C}$ (Note 1)	P_D	1.5	W
Storage Temperature Range	T_{stg}	- 65 to +150	$^\circ\text{C}$
Junction Temperature Range	T_J	- 55 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Device mounted on an epoxy printed circuit board 1.575 inches x 1.575 inches x 0.059 inches; mounting pad for the collector lead min. 0.93 inches².

THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	83.3	$^\circ\text{C}/\text{W}$
Lead Temperature for Soldering, 0.0625" from case Time in Solder Bath	T_L	260 10	$^\circ\text{C}$ Sec

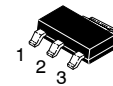
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



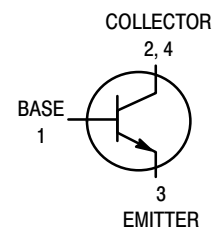
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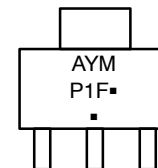
SOT-223 PACKAGE NPN SILICON TRANSISTOR SURFACE MOUNT



SOT-223 (TO-261)
CASE 318E-04
STYLE 1



MARKING DIAGRAM



A = Assembly Location
Y = Year
M = Month Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
PZT222AT1G	SOT-223 (Pb-Free)	1,000 Tape & Reel
SPZT222AT1G	SOT-223 (Pb-Free)	1,000 Tape & Reel
PZT222AT3G	SOT-223 (Pb-Free)	4,000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PZT2222A

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage (I _C = 10 mA _{dc} , I _B = 0)	V _{(BR)CEO}	40	-	V _{dc}
Collector-Base Breakdown Voltage (I _C = 10 μA _{dc} , I _E = 0)	V _{(BR)CBO}	75	-	V _{dc}
Emitter-Base Breakdown Voltage (I _E = 10 μA _{dc} , I _C = 0)	V _{(BR)EBO}	6.0	-	V _{dc}
Base-Emitter Cutoff Current (V _{CE} = 60 V _{dc} , V _{BE} = -3.0 V _{dc})	I _{BEX}	-	20	nA _{dc}
Collector-Emitter Cutoff Current (V _{CE} = 60 V _{dc} , V _{BE} = -3.0 V _{dc})	I _{CEX}	-	10	nA _{dc}
Emitter-Base Cutoff Current (V _{EB} = 3.0 V _{dc} , I _C = 0)	I _{EBO}	-	100	nA _{dc}
Collector-Base Cutoff Current (V _{CB} = 60 V _{dc} , I _E = 0) (V _{CB} = 60 V _{dc} , I _E = 0, T _A = 125°C)	I _{CBO}	- -	10 10	nA _{dc} μA _{dc}

ON CHARACTERISTICS

DC Current Gain (I _C = 0.1 mA _{dc} , V _{CE} = 10 V _{dc}) (I _C = 1.0 mA _{dc} , V _{CE} = 10 V _{dc}) (I _C = 10 mA _{dc} , V _{CE} = 10 V _{dc}) (I _C = 10 mA _{dc} , V _{CE} = 10 V _{dc} , T _A = -55°C) (I _C = 150 mA _{dc} , V _{CE} = 10 V _{dc}) (I _C = 150 mA _{dc} , V _{CE} = 1.0 V _{dc}) (I _C = 500 mA _{dc} , V _{CE} = 10 V _{dc})	h _{FE}	35 50 70 35 100 50 40	- - - - 300 - -	-
Collector-Emitter Saturation Voltages (I _C = 150 mA _{dc} , I _B = 15 mA _{dc}) (I _C = 500 mA _{dc} , I _B = 50 mA _{dc})	V _{CE(sat)}	- -	0.3 1.0	V _{dc}
Base-Emitter Saturation Voltages (I _C = 150 mA _{dc} , I _B = 15 mA _{dc}) (I _C = 500 mA _{dc} , I _B = 50 mA _{dc})	V _{BE(sat)}	0.6 -	1.2 2.0	V _{dc}
Input Impedance (V _{CE} = 10 V _{dc} , I _C = 1.0 mA _{dc} , f = 1.0 kHz) (V _{CE} = 10 V _{dc} , I _C = 10 mA _{dc} , f = 1.0 kHz)	h _{ie}	2.0 0.25	8.0 1.25	kΩ
Voltage Feedback Ratio (V _{CE} = 10 V _{dc} , I _C = 1.0 mA _{dc} , f = 1.0 kHz) (V _{CE} = 10 V _{dc} , I _C = 10 mA _{dc} , f = 1.0 kHz)	h _{re}	- -	8.0x10 ⁻⁴ 4.0x10 ⁻⁴	-
Small-Signal Current Gain (V _{CE} = 10 V _{dc} , I _C = 1.0 mA _{dc} , f = 1.0 kHz) (V _{CE} = 10 V _{dc} , I _C = 10 mA _{dc} , f = 1.0 kHz)	h _{fe}	50 75	300 375	-
Output Admittance (V _{CE} = 10 V _{dc} , I _C = 1.0 mA _{dc} , f = 1.0 kHz) (V _{CE} = 10 V _{dc} , I _C = 10 mA _{dc} , f = 1.0 kHz)	h _{oe}	5.0 25	35 200	μmhos
Noise Figure (V _{CE} = 10 V _{dc} , I _C = 100 μA _{dc} , f = 1.0 kHz)	F	-	4.0	dB

DYNAMIC CHARACTERISTICS

Current-Gain – Bandwidth Product (I _C = 20 mA _{dc} , V _{CE} = 20 V _{dc} , f = 100 MHz)	f _T	300	-	MHz
Output Capacitance (V _{CB} = 10 V _{dc} , I _E = 0, f = 1.0 MHz)	C _c	-	8.0	pF
Input Capacitance (V _{EB} = 0.5 V _{dc} , I _C = 0, f = 1.0 MHz)	C _e	-	25	pF

SWITCHING TIMES (T_A = 25°C)

Delay Time	(V _{CC} = 30 V _{dc} , I _C = 150 mA _{dc} , I _{B(on)} = 15 mA _{dc} , V _{EB(off)} = 0.5 V _{dc}) Figure 1	t _d	-	10	ns
Rise Time		t _r	-	25	
Storage Time	(V _{CC} = 30 V _{dc} , I _C = 150 mA _{dc} , I _{B(on)} = I _{B(off)} = 15 mA _{dc}) Figure 2	t _s	-	225	ns
Fall Time		t _f	-	60	

PZT2222A

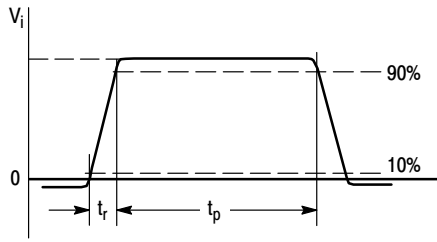


Figure 1. Input Waveform and Test Circuit for Determining Delay Time and Rise Time

$V_i = -0.5 \text{ V to } +9.9 \text{ V}$, $V_{CC} = +30 \text{ V}$, $R_1 = 619 \Omega$, $R_2 = 200 \Omega$.

PULSE GENERATOR:

PULSE DURATION t_p 3 200 ns
RISE TIME t_r 3 2 ns
DUTY FACTOR δ = 0.02

OSCILLOSCOPE:

INPUT IMPEDANCE $Z_i > 100 \text{ k}\Omega$
INPUT CAPACITANCE $C_i < 12 \text{ pF}$
RISE TIME $t_r < 5 \text{ ns}$

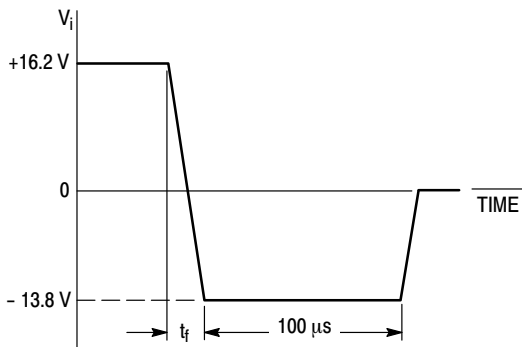


Figure 2. Input Waveform and Test Circuit for Determining Storage Time and Fall Time

TYPICAL CHARACTERISTICS

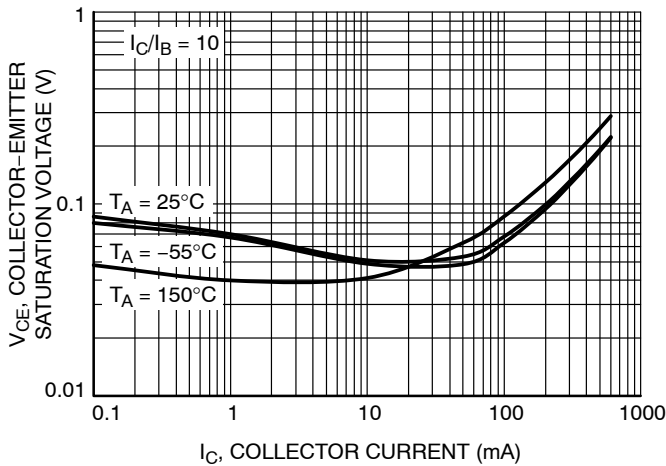


Figure 3. Collector Emitter Saturation Voltage vs. Collector Current

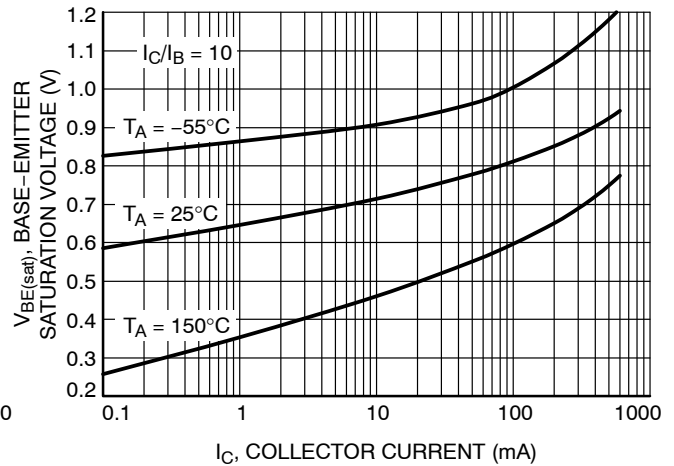


Figure 4. Base Emitter Saturation Voltage vs. Collector Current

TYPICAL CHARACTERISTICS

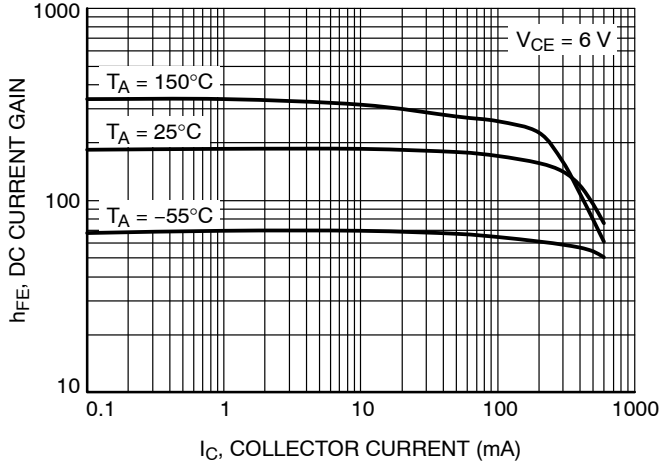


Figure 5. DC Current Gain vs. Collector Current

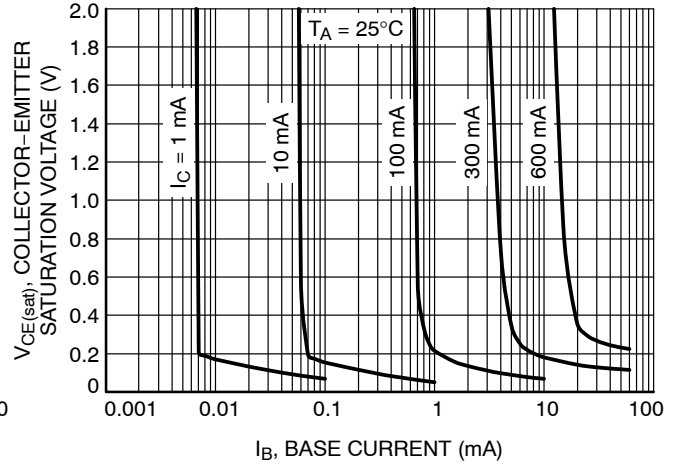


Figure 6. Saturation Region

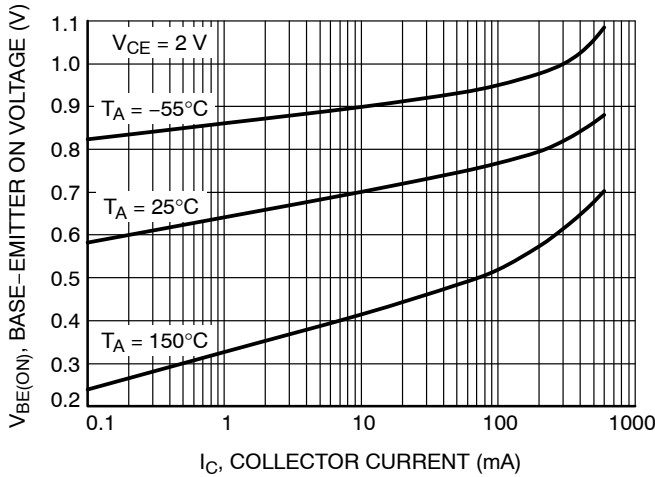


Figure 7. Base-Emitter Turn-On Voltage vs. Collector Current

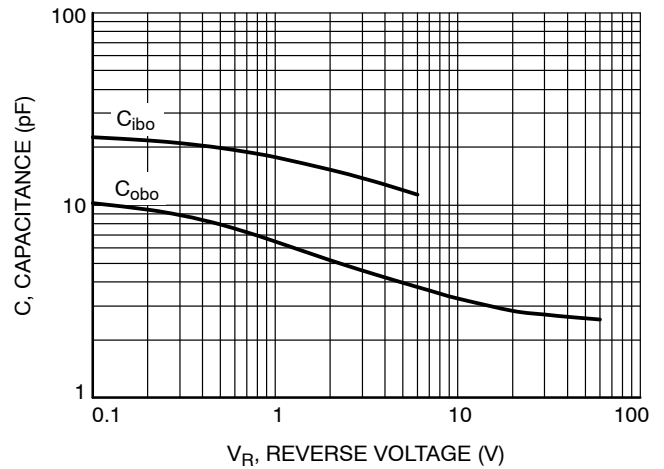


Figure 8. Capacitance

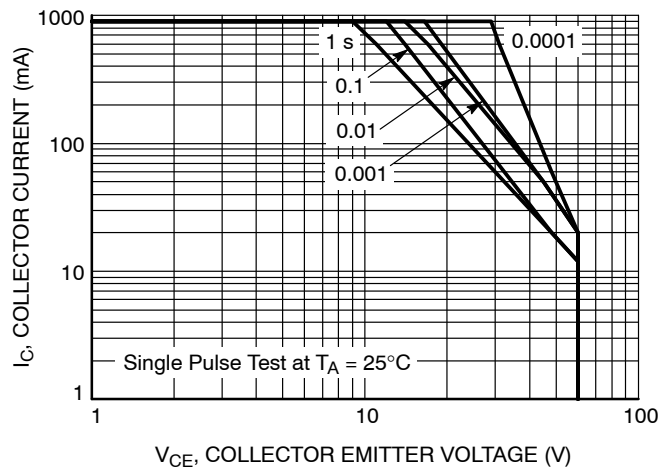


Figure 9. Safe Operating Area

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